

Power transistor (60V, 3A)

• Features

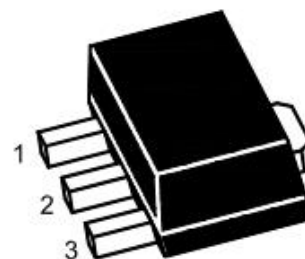
- 1) High speed switching. (Tf : Typ. : 30ns at IC = 3A)
- 2) Low saturation voltage, typically (Typ. : 200mV at IC = 2A, IB = 200mA)
- 3) Strong discharge power for inductive load and capacitance load.
- 4) Complements the 2SA2071.

• Applications

NPN Silicon epitaxial planar transistor

• Structure

Low frequency amplifier High speed switching



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

• Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	VCBO	60	V
Collector-emitter voltage	VCEO	60	V
Emitter-base voltage	VEBO	6	V
Collector current	IC	3	A
	ICP	6	A *1
Power dissipation	PC	500	mW *2
	PC	2.0	W *3
Junction temperature	Tj	150	°C
Range of storage temperature	Tstg	-55~+150	°C

*1 Pw=100ms

*2 Each terminal mounted on a recommended land.

*3 Mounted on a 40x40x0.7(mm) ceramic substrate

• hFE RANK

Q	R
120-270	180-390

• **Electrical characteristics (Ta=25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	60	-	-	V	IC=100μA
Collector-emitter breakdown voltage	BVCEO	60	-	-	V	IC=1mA
Emitter-base breakdown voltage	BVEBO	6	-	-	V	IE=100μA
Collector cut-off current	ICBO	-	-	1.0	μA	VCB=40V
Emitter cut-off current	IEBO	-	-	1.0	μA	VEB=4V
Collector-emitter saturation voltage	VCE(sat)	-	200	500	mV	IC=2A, IB=200mA *1
DC current gain	hFE	120	-	390	-	VCE=2V, IC=100mA
Transition frequency	fT	-	200	-	MHz	VCE=10V, IE=-100mA, f=10MHz *
Collector output capacitance	Cob	-	20	-	pF	VCB=10V, IE=0mA, f=1MHz
Turn-on time	Ton	-	50	-	ns	IC=3A, IB1=300mA, IB2=-300mA, VCC 25V *2
Storage time	Tstg	-	150	-	ns	
Fall time	Tf	-	30	-	ns	

*1 Non repetitive pulse
*2 See switching characteristics measurement circuits

• **Electrical characteristic curves**

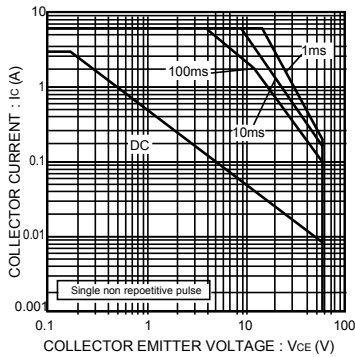


Fig.1 Safe operating area

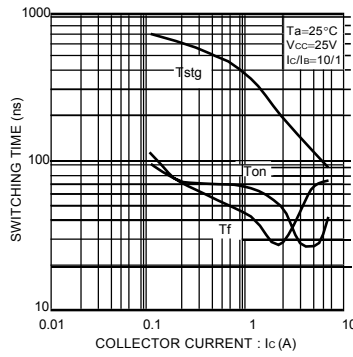


Fig.2 Switching Time

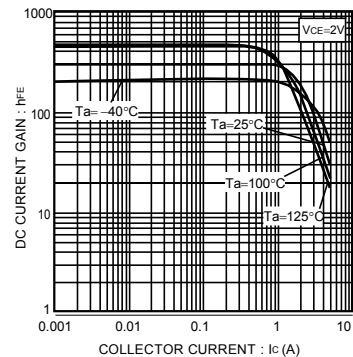


Fig.3 DC current gain vs. collector current

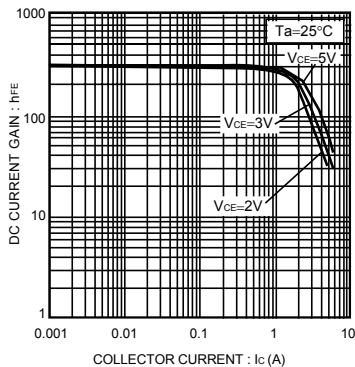


Fig.4 DC current gain vs. collector current

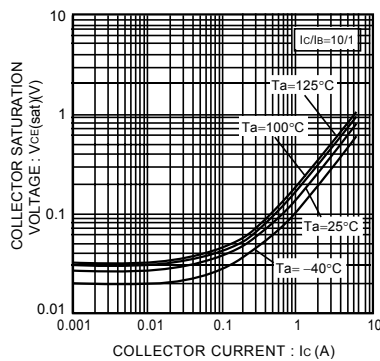


Fig.5 Collector-emitter saturation voltage vs. Collector Current

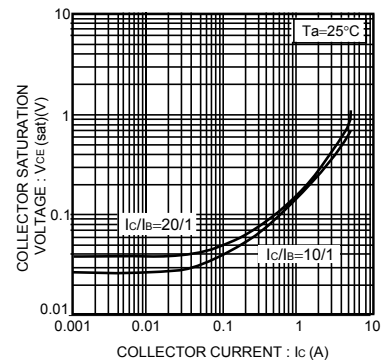


Fig.6 Collector-emitter saturation voltage vs. collector current

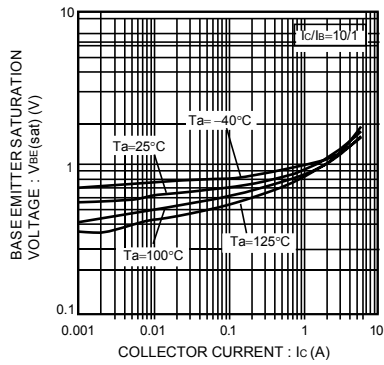


Fig.7 Base-emitter saturation voltage vs. collector current

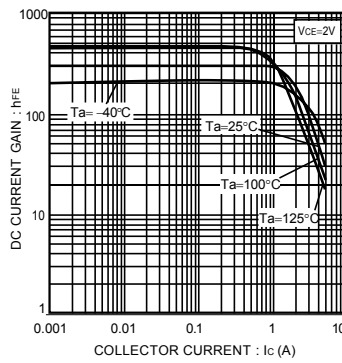


Fig.3 DC current gain vs. collector current

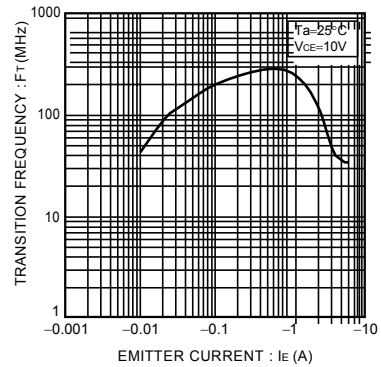


Fig.9 Transition frequency

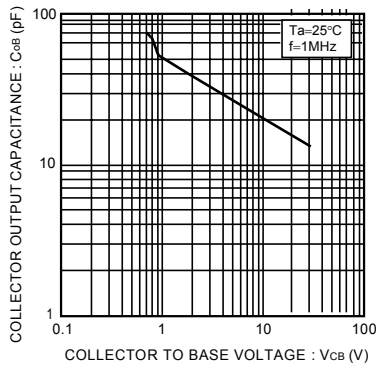
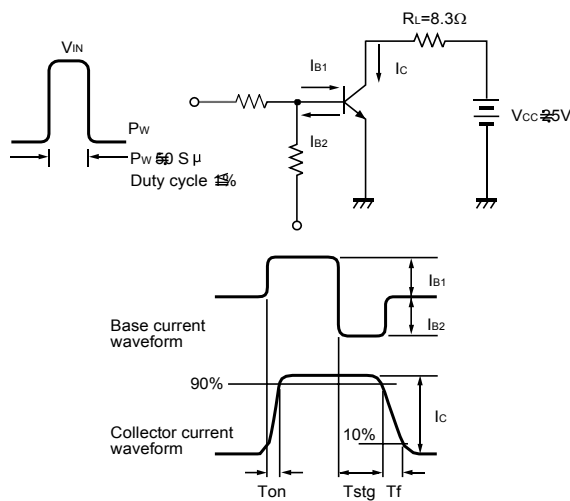
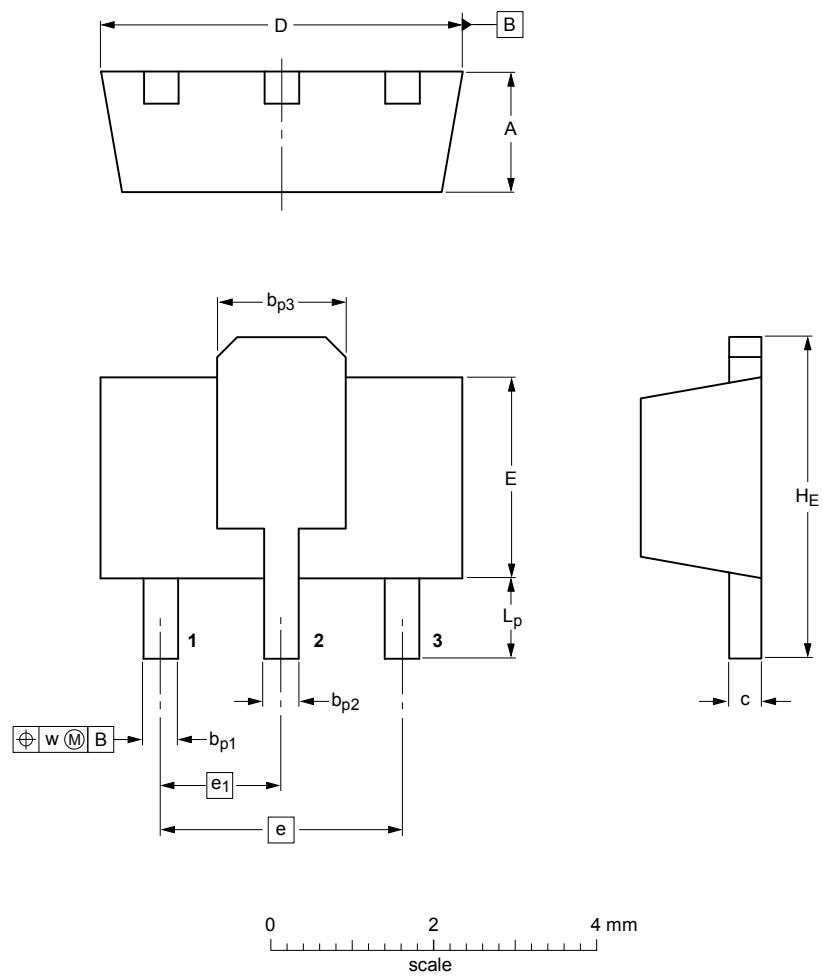


Fig.10 Collector output capacitance

• **Switching characteristics measurement circuits**



SOT-89 PACKAGE OUTLINE



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [SLKORMICRO manufacturer](#):

Other Similar products are found below :

[BC559C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [NJVMJD148T4G](#) [NTE16](#) [NTE195A](#) [IMX9T110](#) [2N4401-A](#) [2N4403](#) [2N6728](#)
[2SA1419T-TD-H](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [FMC5AT148](#) [2N2369ADCSM](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC4618TLN](#) [CPH6501-](#)
[TL-E](#) [MCH4021-TL-E](#) [Jantx2N5416](#) [US6T6TR](#) [BAX18/A52R](#) [BC556/112](#) [IMZ2AT108](#) [MMST8098T146](#) [UMX21NTR](#) [MCH6102-TL-E](#)
[TTA1452B,S4X\(S](#) [2N3879](#) [NTE13](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [JANTX2N2920L](#) [JANTX2N3735](#) [JANSR2N2222AUB](#)
[CMLT3946EG TR](#) [SNSS40600CF8T1G](#) [CMLT3906EG TR](#) [GRP-DATA-JANS2N2907AUB](#) [GRP-DATA-JANS2N2222AUA](#)
[MMDT3946FL3-7](#) [2N4240](#) [MSB30KH-13](#) [2N2221AUB](#) [2SD1815T-TL-E](#)